

RETRACTION

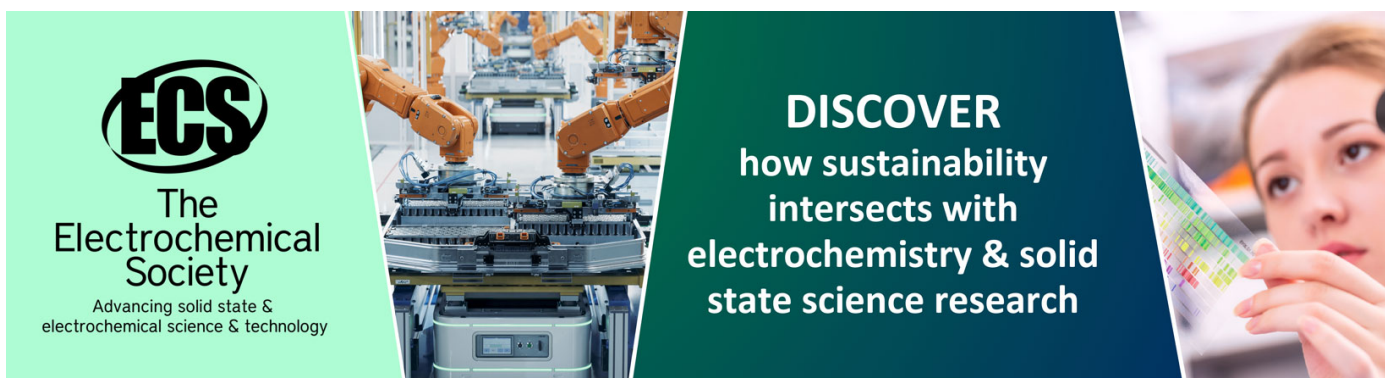
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Retraction: Impact of an ultra-thin ZrTiO_4 buffer layer for long retention characteristics of metal–ferroelectric–insulator–semiconductor capacitor (2016 *J. Phys. D: Appl. Phys.* **49** 185104)

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